

MOSFET – N-Channel, POWERTRENCH®

30 V, 16 A, 14.3 mohm

FDMC8882

Description

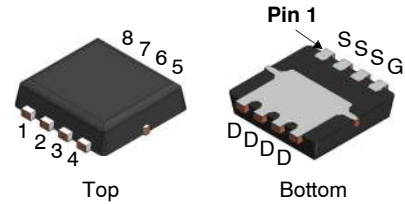
This N-Channel MOSFET is produced using **onsemi**'s advanced POWETRENCH process that has been especially tailored to minimize the on-state resistance. This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

Features

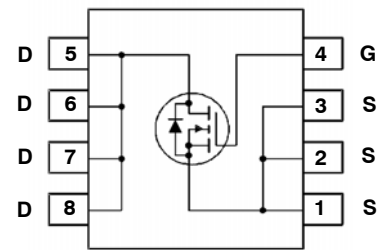
- Max $R_{DS(on)}$ = 14.3 mΩ at $V_{GS} = 10\text{ V}$, $I_D = 10.5\text{ A}$
- Max $R_{DS(on)}$ = 22.5 mΩ at $V_{GS} = 4.5\text{ V}$, $I_D = 8.3\text{ A}$
- High Performance Technology for Extremely Low $R_{DS(on)}$
- Termination is Lead-Free
- RoHS Compliant

Applications

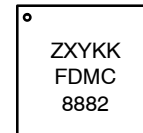
- High Side in DC-DC Buck Converters
- Notebook Battery Power Management
- Load Switch in Notebook



**WDFN8 3.3x3.3, 0.65P
 CASE 511DR**



MARKING DIAGRAM



- Z = Assembly Plant Code
- XY = Date Code (Year & Week)
- KK = Lot Traceability Code
- FDMC8882 = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping†
FDMC8882	WDFN8 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

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MOSFET MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Ratings	Unit	
V_{DS}	Drain to Source Voltage		30	V	
V_{GS}	Gate to Source Voltage		± 20	V	
I_D	Drain Current	Continuous (Package Limited)	$T_C = 25^\circ\text{C}$	16	A
		Continuous (Silicon Limited)	$T_C = 25^\circ\text{C}$	34	
		Continuous	$T_A = 25^\circ\text{C}$ (Note 1a)	10.5	A
		Pulsed	-	40	
P_D	Power Dissipation		$T_C = 25^\circ\text{C}$	18	W
	Power Dissipation		$T_A = 25^\circ\text{C}$ (Note 1a)	2.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to +150	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	6.6	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	53	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV_{DSS}	Drain-to-Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{V}$	30	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, referenced to 25°C	-	25	-	$\text{mV}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{V}, V_{GS} = 0 \text{V}$	-	-	1	μA
		$V_{DS} = 24 \text{V}, V_{GS} = 0 \text{V}, T_J = 125^\circ\text{C}$	-	-	250	
I_{GSS}	Gate-to-Source Leakage Current	$V_{GS} = \pm 20 \text{V}, V_{DS} = 0 \text{V}$	-	-	± 100	nA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate-to-Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	1.2	1.9	2.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate-to-Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, referenced to 25°C	-	-5	-	$\text{mV}/^\circ\text{C}$
$R_{DS(on)}$	Static Drain-to-Source On Resistance	$V_{GS} = 10 \text{V}, I_D = 10.5 \text{A}$	-	12.4	14.3	$\text{m}\Omega$
		$V_{GS} = 4.5 \text{V}, I_D = 8.3 \text{A}$	-	16.0	22.5	
		$V_{GS} = 10 \text{V}, I_D = 10.5 \text{A}, T_J = 125^\circ\text{C}$	-	17.4	-	
g_{FS}	Forward Transconductance	$V_{DS} = 5 \text{V}, I_D = 10.5 \text{A}$	-	33	-	S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 15 \text{V}, V_{GS} = 0 \text{V}, f = 1 \text{MHz}$	-	710	945	pF
C_{oss}	Output Capacitance		-	140	185	pF
C_{rss}	Reverse Transfer Capacitance		-	90	135	pF
R_g	Gate Resistance		-	1.0	-	Ω

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}$, $I_D = 10.5\text{ A}$, $V_{GS} = 10\text{ V}$, $R_{GEN} = 6\ \Omega$	-	7	14	ns
t_r	Rise Time		-	3	10	
$t_{d(off)}$	Turn-Off Delay Time		-	17	30	
t_f	Fall Time		-	2	10	
$Q_{g(tot)}$	Total Gate Charge	$V_{GS} = 0\text{ V to }10\text{ V}$, $V_{DD} = 15\text{ V}$, $I_D = 10.5\text{ A}$	-	14	20	nC
	Total Gate Charge	$V_{GS} = 0\text{ V to }4.5\text{ V}$, $V_{DD} = 15\text{ V}$, $I_D = 10.5\text{ A}$	-	7	10	
Q_{gs}	Gate-to-Source Charge	$V_{DD} = 15\text{ V}$, $I_D = 10.5\text{ A}$	-	2.3	-	
Q_{gd}	Gate-to-Drain "Miller" Charge	$V_{DD} = 15\text{ V}$, $I_D = 10.5\text{ A}$	-	2.8	-	

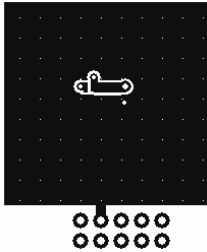
DRAIN-SOURCE DIODE CHARACTERISTICS

V_{SD}	Source-to-Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 10.5\text{ A}$ (Note 2)	-	0.88	1.2	V
		$V_{GS} = 0\text{ V}$, $I_S = 1.9\text{ A}$ (Note 2)	-	0.76	1.2	
t_{rr}	Reverse Recovery Time	$I_F = 10.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	-	16	28	ns
Q_{rr}	Reverse Recovery Charge		-	4.4	10	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

- $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



- 53°C/W when mounted on a 1 in² pad of 2 oz copper



- 125°C/W when mounted on a minimum pad of 2 oz copper

- Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

TYPICAL CHARACTERISTICS

($T_J = 25^\circ\text{C}$ unless otherwise noted)

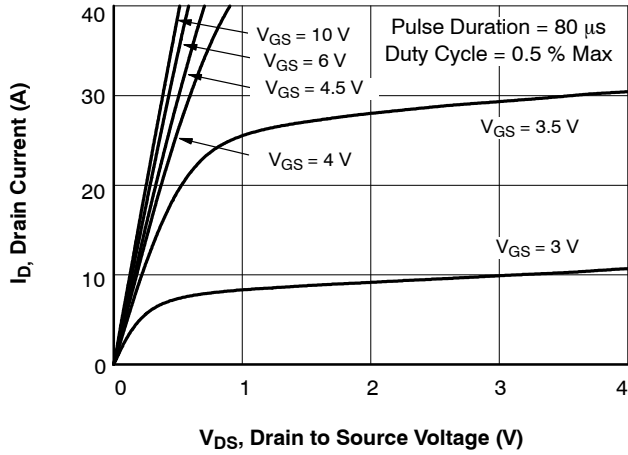


Figure 1. On-Region Characteristics

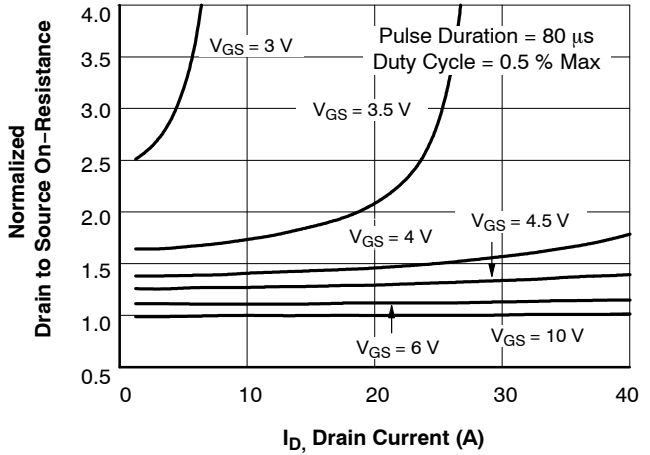


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

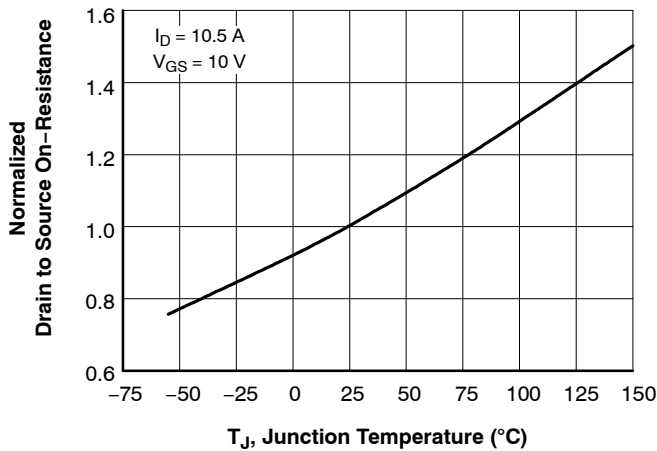


Figure 3. Normalized On-Resistance vs. Junction Temperature

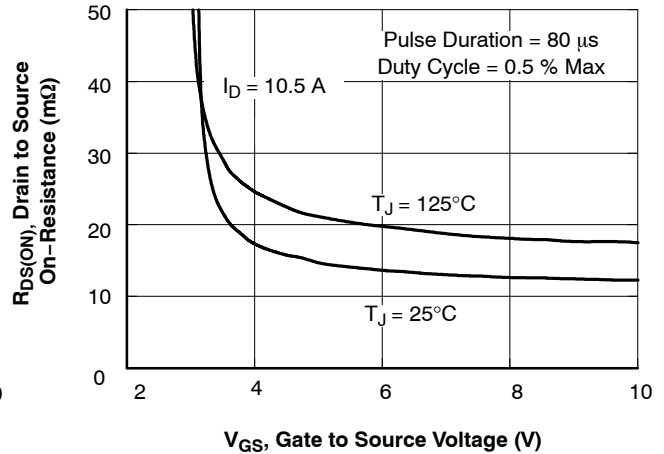


Figure 4. On-Resistance vs. Gate to Source Voltage

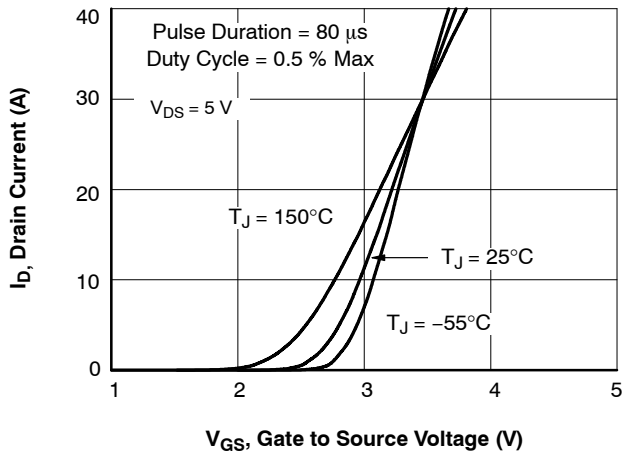


Figure 5. Transfer Characteristics

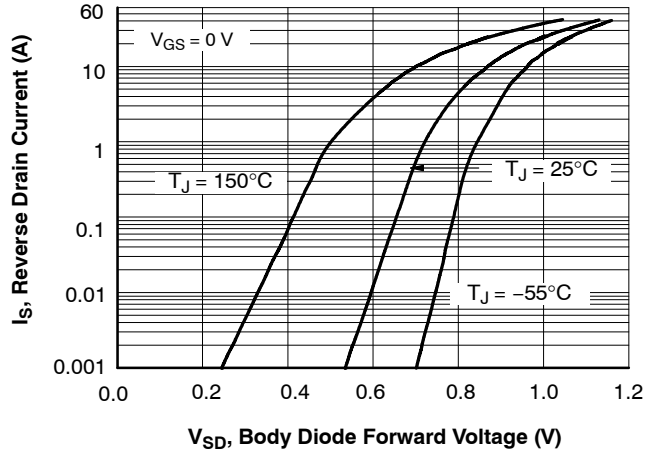


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (continued)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

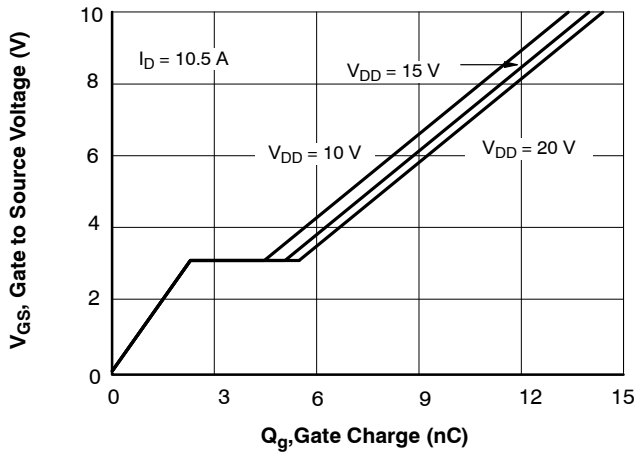


Figure 7. Gate Charge Characteristics

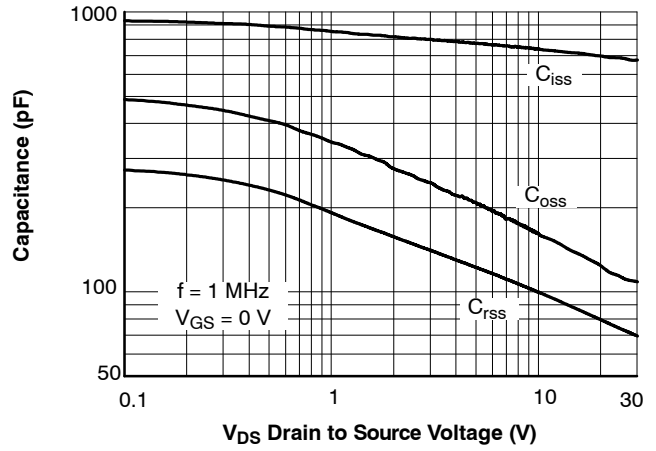


Figure 8. Capacitance vs Drain to Source Voltage

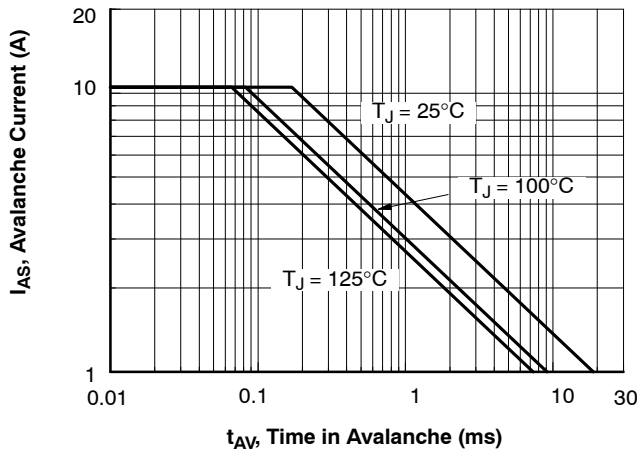


Figure 9. Unclamped Inductive Switching Capability

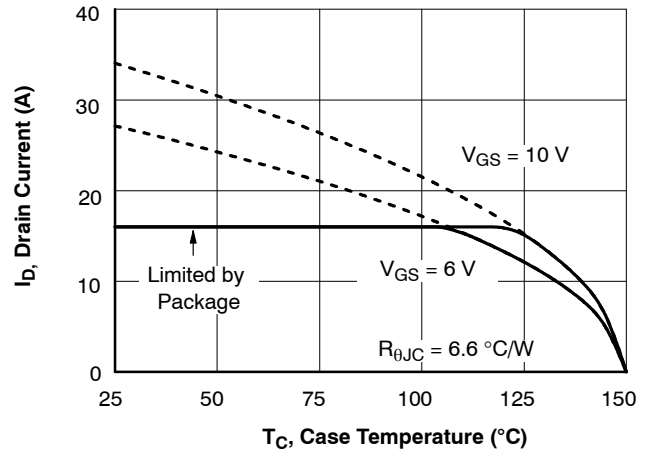


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

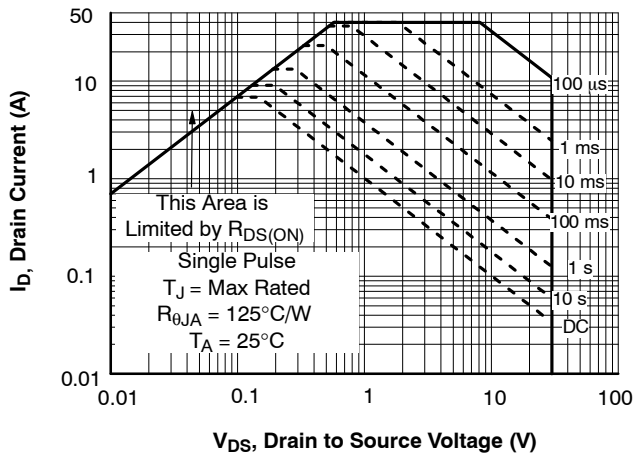


Figure 11. Forward Bias Safe Operating Area

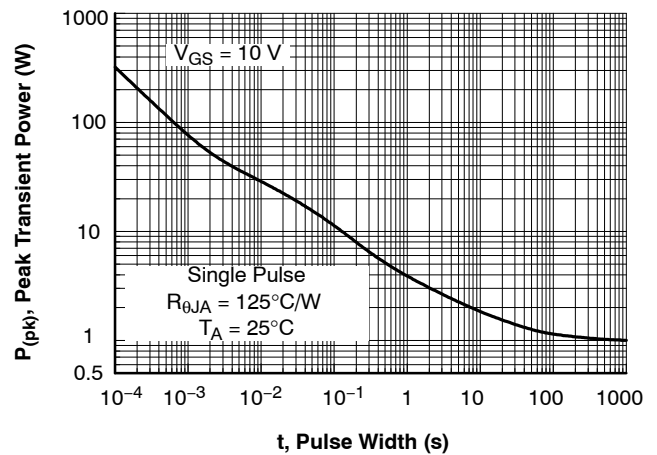


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (continued)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

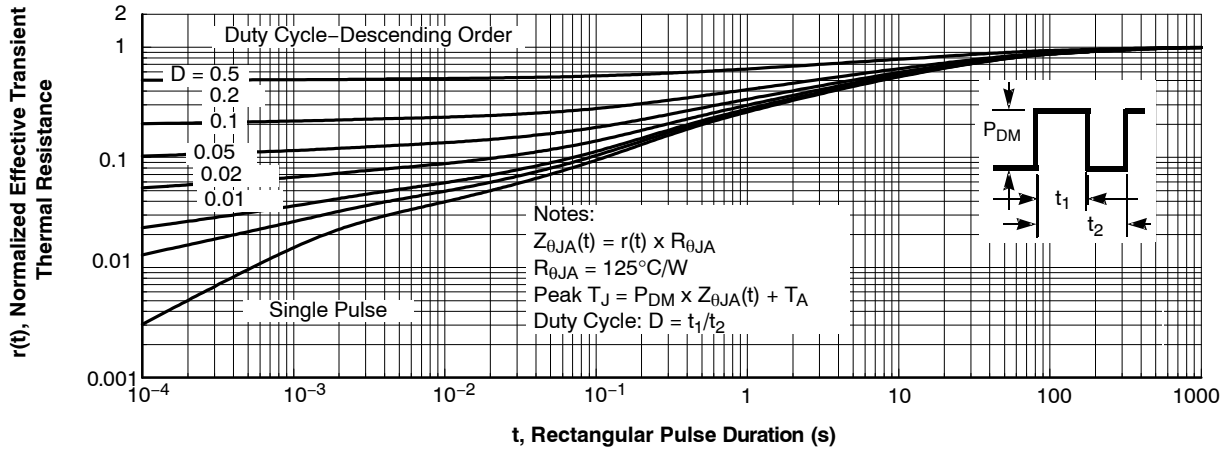


Figure 13. Transient Thermal Response Curve

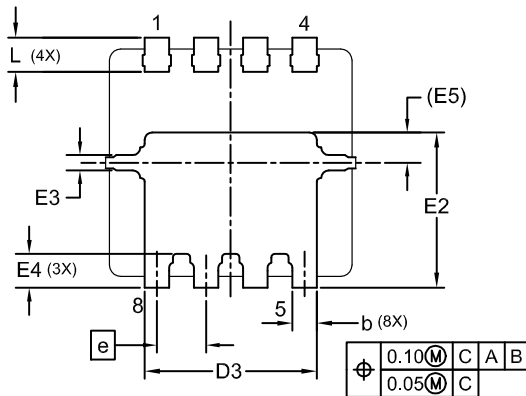
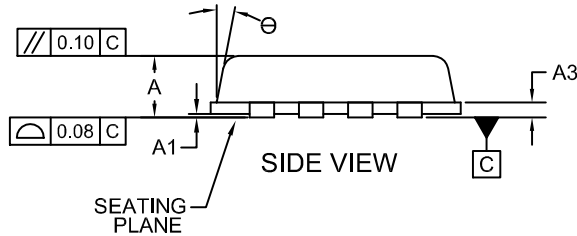
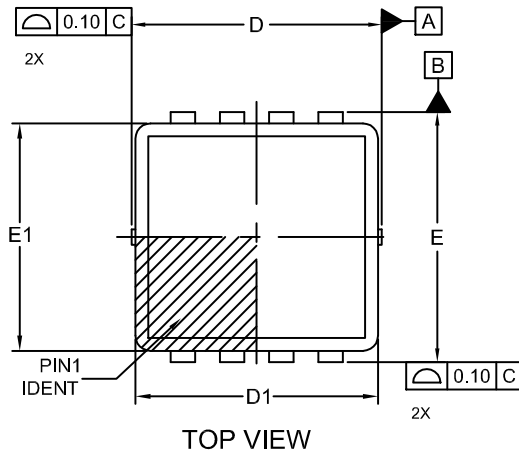
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



WDFN8 3.3x3.3, 0.65P
CASE 511DR
ISSUE B

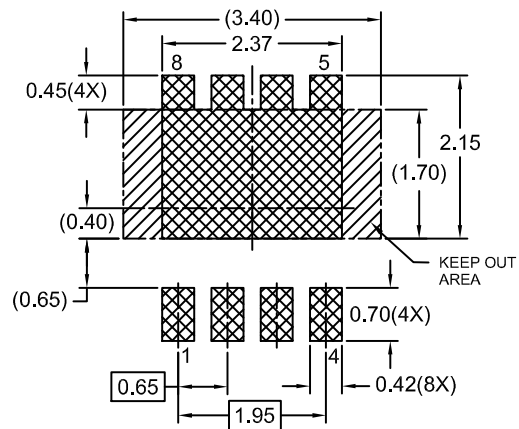
DATE 02 FEB 2022



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	-	0.05
A3	0.15	0.20	0.25
b	0.27	0.32	0.37
D	3.20	3.30	3.40
D1	3.10	3.20	3.30
D3	2.17	2.27	2.37
E	3.20	3.30	3.40
E1	2.90	3.00	3.10
E2	1.95	2.05	2.15
E3	0.15	0.20	0.25
E4	0.30	0.40	0.50
E5	0.40 REF		
e	0.65 BSC		
L	0.30	0.40	0.50
θ	0°	-	12°

NOTES:

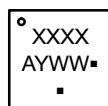
- A. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- B. SEATING PLANE IS DEFINED BY TERMINAL TIPS ONLY
- C. BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH PROTRUSIONS NOR GATE BURRS. MOLD FLASH PROTRUSION OR GATE BURR DOES NOT EXCEED 0.150MM.



RECOMMENDED LAND PATTERN

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

(Note: Microdot may be in either location)

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